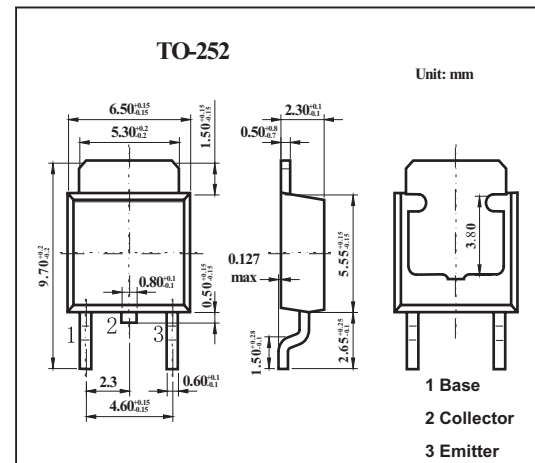


NPN Triple Diffused Planar Silicon Transistor

2SC4003

■ Features

- High breakdown voltage
- Adoption of MBIT process
- Excellent hFE linearity

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

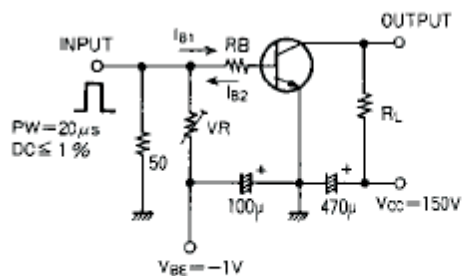
Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	400	V
Collector to emitter voltage	V_{CEO}	400	V
Emitter to base voltage	V_{EBO}	5	V
Collector current (DC)	I_C	200	mA
Collector current (Pulse)	I_{cp}	400	mA
Total Power dissipation $T_a = 25^\circ\text{C}$ $T_C = 25^\circ\text{C}$	P_C	1	W
		10	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

2SC4003

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
collector cutoff current	I_{CBO}	$V_{CB}=300\text{V}, I_E=0$			0.1	μA
emitter cutoff current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current Gain	h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	60		200	
Gain-Bandwidth Product	f_T	$V_{CE}=30\text{V}, I_C=10\text{mA}$		70		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	400			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, R_{BE}=\infty$	400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Output Capacitance	C_{ob}	$V_{CB}=30\text{V}, f=1\text{MHz}$		4		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=30\text{V}, f=1\text{MHz}$		3		pF
Turn-ON Time	t_{on}	see specified Test Circuit		0.25		μs
Turn-OFF Time	t_{off}			5		μs

■ Switching Time Test Circuit

Unit (Resistance : Ω , Capacitance : F)
 $10I_{B1} = -10I_{B2} = I_C = 50\text{mA}$
 $R_L = 3\text{k}\Omega, R_B = 200\Omega$ at $I_C = 50\text{mA}$
■ h_{FE} Classification

Marking	D	E
h_{FE}	60 to 120	100 to 200